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- EPIC™ (Enhanced-Performance Implanted CMOS) Process
- Typical V<sub>OLP</sub> (Output Ground Bounce)
  <0.8 V at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C
- Typical V<sub>OHV</sub> (Output V<sub>OH</sub> Undershoot)
  >2.3 V at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C
- 2-V to 5.5-V V<sub>CC</sub> Operation
- Support Mixed-Mode Voltage Operation on All Ports
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (D, NS), Shrink Small-Outline (DB), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages, Ceramic Flat (W) Packages, Chip Carriers (FK), and DIPs (J)

#### description

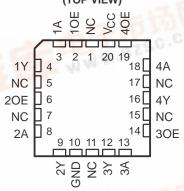
These quadruple bus buffer gates are designed for 2-V to 5.5-V V<sub>CC</sub> operation.

The 'LV126A devices feature independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable (OE) input is low.

SN54LV126A . . . J OR W PACKAGE SN74LV126A . . . D, DB, DGV, NS, OR PW PACKAGE (TOP VIEW)



SN54LV126A . . . FK PACKAGE (TOP VIEW)



NC – No internal connection

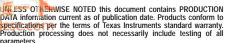
To ensure the high-impedance state during power up or power down, OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

The SN54LV126A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV126A is characterized for operation from –40°C to 85°C.

## FUNCTION TABLE (each buffer)

INPL	JTS	OUTPUT
OE	Α	Υ
Н	Н	Н
Н	L	L
C.O.	Χ	Z

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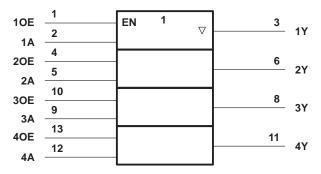
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## SN54LV126A, SN74LV126A QUADRUPLE BUS BUFFER GATES WITH 3-STATE OUTPUTS

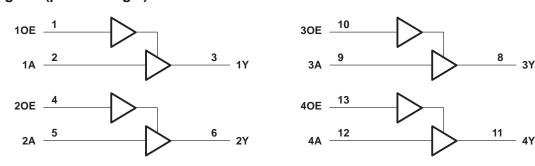
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#### logic symbol†



<sup>&</sup>lt;sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the D, DB, DGV, J, NS, PW, and W packages.

### logic diagram (positive logic)



Pin numbers shown are for the D, DB, DGV, J, NS, PW, and W packages.

## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V <sub>CC</sub>		0.5 V to 7 V
Input voltage range, V <sub>I</sub> (see Note 1)		
Voltage range applied to any output in the high	n-impedance	
or power-off state, V <sub>O</sub> (see Note 1)		0.5 V to 7 V
Output voltage range, VO (see Notes 1 and 2)		
Input clamp current, $I_{IK}$ ( $V_I < 0$ )		
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0 or V <sub>O</sub> > V <sub>C</sub>		
Continuous output current, $I_O(V_O = 0 \text{ to } V_{CC})$		
Continuous current through V <sub>CC</sub> or GND		±70 mA
Package thermal impedance, θ <sub>JA</sub> (see Note 3)	: D package	86°C/W
	DB package	96°C/W
	DGV package	127°C/W
	NS package	76°C/W
	PW package	113°C/W
Operating free-air temperature range, T <sub>A</sub>		–40°C to 85°C
Storage temperature range, T <sub>stq</sub>		–65°C to 150°C

<sup>‡</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
  - 2. This value is limited to 5.5 V maximum.
  - 3. The package thermal impedance is calculated in accordance with JESD 51.



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## recommended operating conditions (see Note 4)

			SN54LV	′126A	SN74L	UNIT	
			MIN	MAX	MIN MAX		UNII
Vcc	Supply voltage		2	5.5	2	5.5	V
		V <sub>CC</sub> = 2 V	1.5		1.5		
\/	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	V <sub>CC</sub> ×0.7		$V_{CC} \times 0.7$		\ <sub>\</sub>
VIH	nigii-ievei iriput voitage	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	V <sub>CC</sub> ×0.7		$V_{CC} \times 0.7$		ľ
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	V <sub>CC</sub> ×0.7		$V_{CC} \times 0.7$		
		V <sub>CC</sub> = 2 V		0.5		0.5	
\/	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	V	CC × 0.3	V	$^{\prime}$ CC $\times$ 0.3	V
VIL	Low-level input voltage	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	V	CC × 0.3	V	V <sub>CC</sub> ×0.3	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	V	CC × 0.3	V	CC×0.3	
٧ <sub>I</sub>	Input voltage		0	5.5	0	5.5	V
\/o	Output voltage	High or low state	0	VCC	0	Vcc	V
۷o		3-state	0 2	5.5	0	5.5	ľ
		V <sub>CC</sub> = 2 V	20	<del>-</del> 50		-50	μΑ
	High-level output current	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	200	-2		-2	
ІОН	riigii-ievei output current	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	0	-8		-8	mA
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		-16		-16	
		V <sub>CC</sub> = 2 V		50		50	μΑ
	Low lovel output ourrent	V <sub>CC</sub> = 2.3 V to 2.7 V		2		2	
lOL	Low-level output current	V <sub>CC</sub> = 3 V to 3.6 V		8		8	mA
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		16		16	
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	0	200	0	200	
Δt/Δν	Input transition rise or fall rate	V <sub>CC</sub> = 3 V to 3.6 V	0	100	0	100	ns/V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0	20	0	20	
TA	Operating free-air temperature	<u> </u>	-55	125	-40	85	°C

NOTE 4: All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

# electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	.,	SN54LV126A	SN74LV126A	UNIT
PARAMETER	TEST CONDITIONS	VCC	MIN TYP MAX	MIN TYP MAX	UNIT
	$I_{OH} = -50 \mu A$	2 V to 5.5 V	V <sub>CC</sub> -0.1	V <sub>CC</sub> -0.1	
VOH	$I_{OH} = -2 \text{ mA}$	2.3 V	2	2	V
VOH .	$I_{OH} = -8 \text{ mA}$	3 V	2.48	2.48	v
	I <sub>OH</sub> = -16 mA	4.5 V	3.8	3.8	
	I <sub>OL</sub> = 50 μA	2 V to 5.5 V	0.1	0.1	
\/a-	I <sub>OL</sub> = 2 mA	2.3 V	0.4	0.4	V
VOL	I <sub>OL</sub> = 8 mA	3 V	0.44	0.44	V
	I <sub>OL</sub> = 16 mA	4.5 V	0.55	0.55	
lį	$V_I = V_{CC}$ or GND	0 V to 5.5 V	±1	±1	μΑ
loz	$V_O = V_{CC}$ or GND	5.5 V	±5	±5	μΑ
lcc	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V	20	20	μΑ
loff	$V_I$ or $V_O = 0$ to 5.5 $V$	0 V	5	5	μΑ
C <sub>i</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND	3.3 V	1.6	1.6	pF



## SN54LV126A, SN74LV126A QUADRUPLE BUS BUFFER GATES WITH 3-STATE OUTPUTS

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## switching characteristics over recommended operating free-air temperature range, $V_{CC}$ = 2.5 V $\pm$ 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM	то	LOAD	T,	չ = 25°C	;	SN54L	V126A	SN74L\	/126A	UNIT
PARAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
<sup>t</sup> pd	А	Υ			7.1*	13*	1*	15.5*	1	15.5	
t <sub>en</sub>	OE	Υ	C <sub>L</sub> = 15 pF		7.4*	13*	1*	15.5*	1	15.5	ns
<sup>t</sup> dis	OE	Υ			5.7*	14.7*	1*	17*	1	17	
<sup>t</sup> pd	А	Υ			9.2	16.5	15	18.5	1	18.5	
t <sub>en</sub>	OE	Υ	C <sub>L</sub> = 50 pF		9.5	16.5	7	18.5	1	18.5	ns
<sup>t</sup> dis	OE	Υ	CL = 50 pr		8.1	18.2	215	20.5	1	20.5	113
tsk(o)						2	Q			2	

<sup>\*</sup> On products compliant to MIL-PRF-38535, this parameter is not production tested.

## switching characteristics over recommended operating free-air temperature range, $V_{CC}$ = 3.3 V $\pm$ 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM TO		LOAD	T <sub>A</sub> = 25°C		SN54LV126A		SN74LV126A		UNIT	
PARAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
<sup>t</sup> pd	А	Y			5*	8*	1*	9.5*	1	9.5	
t <sub>en</sub>	OE	Υ	C <sub>L</sub> = 15 pF		5.1*	8*	1*	9.5*	1	9.5	ns
<sup>t</sup> dis	OE	Υ			4.4*	9.7*	1*	11.5*	1	11.5	
t <sub>pd</sub>	А	Υ			6.4	11.5	15	13	1	13	
t <sub>en</sub>	OE	Y	C <sub>L</sub> = 50 pF		6.6	11.5	3	13	1	13	ns
<sup>t</sup> dis	OE	Υ	CL = 50 pr		6.1	13.2	<sup>0</sup> 1	15	1	15	113
<sup>t</sup> sk(o)						1.5	Q			1.5	

<sup>\*</sup> On products compliant to MIL-PRF-38535, this parameter is not production tested.

## switching characteristics over recommended operating free-air temperature range, $V_{CC}$ = 5 V $\pm$ 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM TO		LOAD	T <sub>A</sub> = 25°C		SN54LV126A		SN74LV126A		UNIT	
PARAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
<sup>t</sup> pd	А	Υ			3.5*	5.5*	1*	6.5*	1	6.5	
t <sub>en</sub>	OE	Υ	C <sub>L</sub> = 15 pF		3.6*	5.1*	1*	6*	1	6	ns
<sup>t</sup> dis	OE	Υ			3.3*	6.8*	1*	8*	1	8	
t <sub>pd</sub>	А	Υ			4.6	7.5	15	8.5	1	8.5	
t <sub>en</sub>	OE	Υ	C <sub>I</sub> = 50 pF		4.6	7.1	770	8	1	8	ns
<sup>t</sup> dis	OE	Υ	C[ = 50 pr		4.3	8.8	0 1	10	1	10	113
<sup>t</sup> sk(o)						1	8			1	

<sup>\*</sup> On products compliant to MIL-PRF-38535, this parameter is not production tested.



# SN54LV126A, SN74LV126A QUADRUPLE BUS BUFFER GATES WITH 3-STATE OUTPUTS SCES131D - MARCH 1998 - REVISED MAY 2000

## noise characteristics, $V_{CC}$ = 3.3 V, $C_L$ = 50 pF, $T_A$ = 25°C (see Note 5)

	PARAMETER		SN74LV126A			
	PARAMETER	MIN	TYP	MAX	UNIT	
V <sub>OL(P)</sub>	Quiet output, maximum dynamic V <sub>OL</sub>		0.3	0.8	V	
V <sub>OL(V)</sub>	Quiet output, minimum dynamic VOL		-0.2	-0.8	V	
VOH(V)	Quiet output, minimum dynamic VOH		3.1		V	
V <sub>IH(D)</sub>	High-level dynamic input voltage	2.31			V	
V <sub>IL(D)</sub>	Low-level dynamic input voltage			0.97	V	

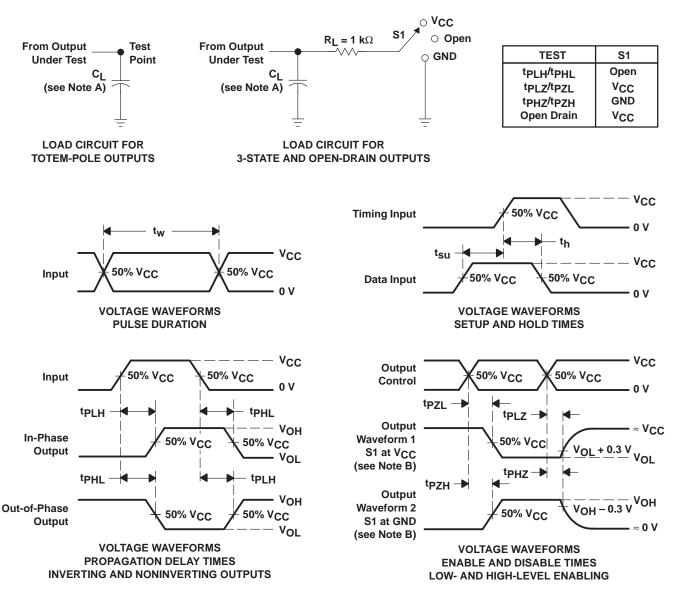
NOTE 5: Characteristics are for surface-mount packages only.

## operating characteristics, $T_A = 25^{\circ}C$

	PARAMETER			TEST CONDITIONS			UNIT
C <sub>pd</sub> Power	Dower dissination conscitones	Outputs enabled	C 50 pE	f _ 10 MU=	3.3 V	14.4	pF
	Power dissipation capacitance		$C_L = 50 \text{ pF},$	f = 10 MHz	5 V	15.9	þг

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#### PARAMETER MEASUREMENT INFORMATION



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1 MHz,  $Z_Q = 50 \Omega$ ,  $t_f \leq 3$  ns,  $t_f \leq 3$  ns.
- D. The outputs are measured one at a time with one input transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
- G. tpHL and tpLH are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



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